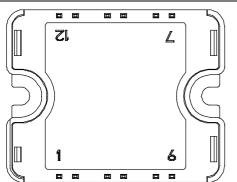


Boost chopper NPT IGBT Power Module

$V_{CES} = 1200V$ $I_{C} = 100A^{*}$ @ Tc = 80°C

$\begin{array}{c} 5 & 6 & 11 \\ \hline CR1 & \hline CR1 & \hline CR2 & \hline 0 & 3 \\ \hline 0 & 4 & \hline 0 & 1 \\ \hline 1 & 2 & 12 \end{array}$ NTC



Pins 1/2; 3/4; 5/6 must be shorted together

t II

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	130*	
I _C	$I_{\rm C}$ Continuous Collector Current $T_{\rm C}$	$T_C = 80^{\circ}C$	100*	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	200	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	735	W
RBSOA	Reverse Bias Safe Operating Area	$T_{\rm J} = 150^{\circ}{\rm C}$	200A @ 1150V	

Specification of IGBT device but output current must be limited to 75A to not exceed a delta of temperature greater than 30°C for the connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings (a) $T_i = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		3.2	3.7	V
V CE(sat)		$I_{\rm C} = 100 {\rm A}$ $T_{\rm j} = 125$	$T_{j} = 125^{\circ}C$		3.9		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 4mA$		4.5	5.5	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		6.5		
C _{oes}	Output Capacitance	$V_{CE} = 25V$		1		nF
Cres	Reverse Transfer Capacitance	f = 1 MHz		0.5		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)		120		
Tr	Rise Time	$V_{GE} = \pm 15V$		50		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 100A$		310		
T _f	Fall Time	$R_G = 5.6\Omega$		20		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C)		130		
Tr	Rise Time	$V_{GE} = \pm 15V$		60		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 100A$		360		ns
T _f	Fall Time	$R_G = 5.6\Omega$		30		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $T_j = 125^{\circ}C$		12		T
E _{off}	Turn-off Switching Energy	$I_{C} = 100A R_{G} = 5.6\Omega $ $T_{j} = 125^{\circ}C$		5		mJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$			100 500	μA
I _F	DC Forward Current		$Tc = 90^{\circ}C$		100	000	А
		$I_{\rm F} = 100 {\rm A}$			2.4	3	
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 150 {\rm A}$			2.7		V
		$I_{\rm F} = 100 {\rm A}$	$T_{j} = 125^{\circ}C$		1.8		
t	t_{rr} Reverse Recovery Time $I_F = 100A$	$T_j = 25^{\circ}C$		385		ns	
۹rr		$I_{\rm F} = 100 {\rm A}$ $V_{\rm R} = 800 {\rm V}$	$T_{j} = 125^{\circ}C$		480		115
Q _{rr}	Reverse Recovery Charge	$di/dt = 200 A/\mu s$ T _j	$T_j = 25^{\circ}C$		1055		nC
Qrr			$T_{j} = 125^{\circ}C$		5240		ne



Thermal and package characteristics

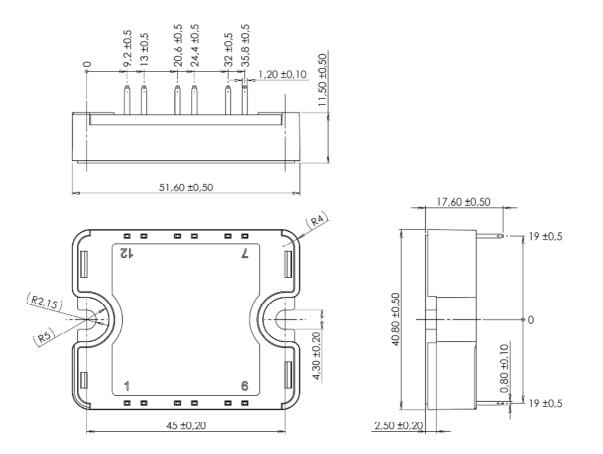
Symbol	Characteristic			Min	Тур	Max	Unit
P	Junction to Case Thermal Resistance	IGBT			0.19	°C/W	
R _{thJC}		Diode			0.55	C/ w	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature					100	
Torque	Mounting torque	To heatsin	k M4	4 2		3	N.m
Wt	Package Weight				80	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP1 Package outline (dimensions in mm)



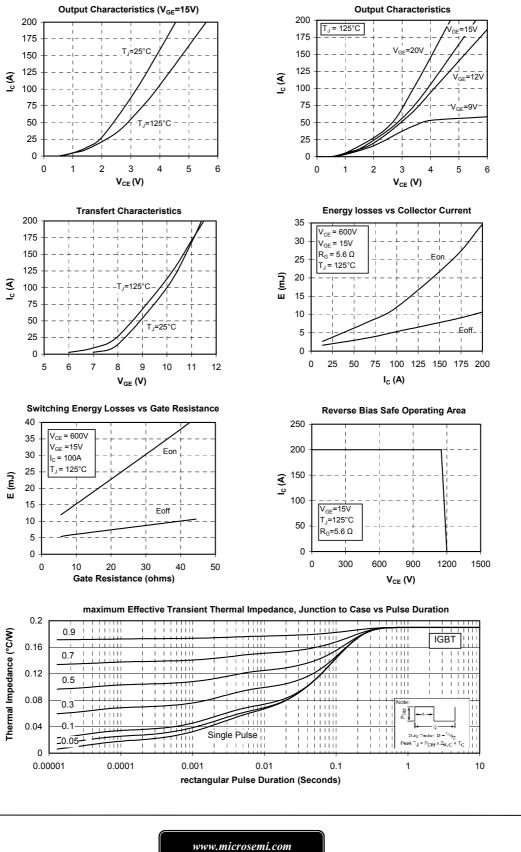
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

www.microsemi.com

3 - 6



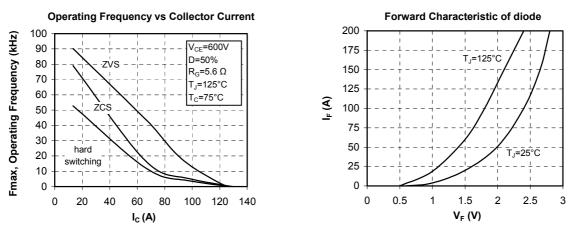
Typical Performance Curve

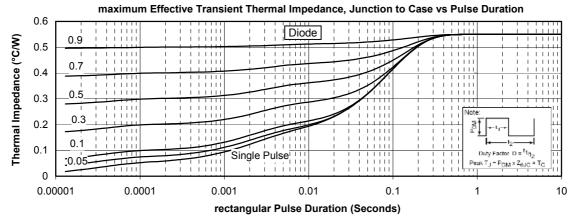


APTGF100DA120T1G

4 - 6







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